JMH65R110ACFD
JMH65R110AEFD

650V SuperJunction Power MOSFET

Features

Product Summary

Parameter	Value	Unit
		Ω





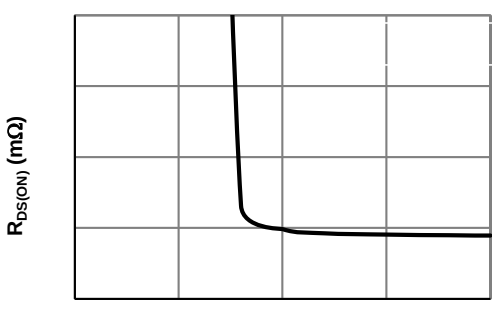
Ordering Information

Device							

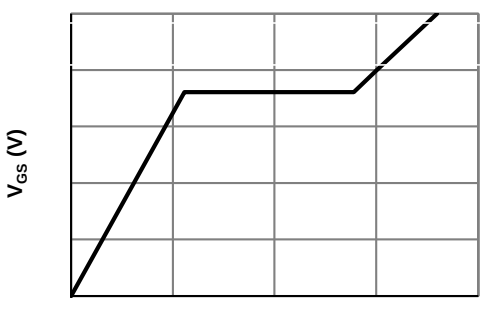
Absolute Maximum Ratings

Parameter			Value	
		GS		V
		I_{DM}		A
		I_{AS}		A
		E_{AS}		mJ
		T_J, T_{STG}		°C

$R_{DS(ON)}$ vs. V_{GS}



Gate Charge



Electrical Characteristics

Parameter	Symbol	Conditions	Min.	Typ.	Max.	Unit
STATIC PARAMETERS						
		μ				
						μ
		μ				
						Ω
						Ω
DYNAMIC PARAMETERS (5)						
						Ω
SWITCHING PARAMETERS (5)						
		/μs				
						μ

Parameter	Symbol	Unit
	θ	
	θ	

Notes:

Typical Electrical & Thermal Characteristics

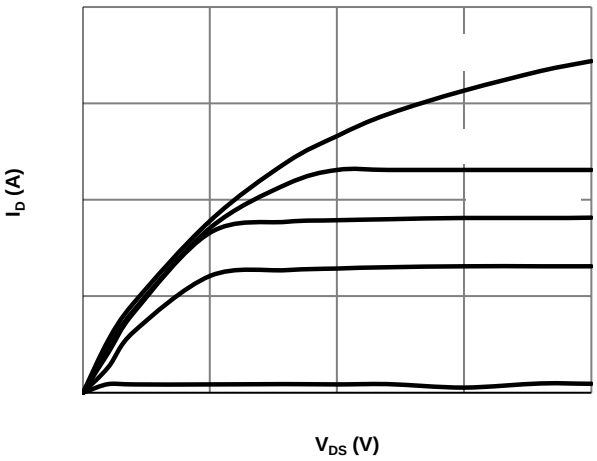


Figure 1: Saturation Characteristics

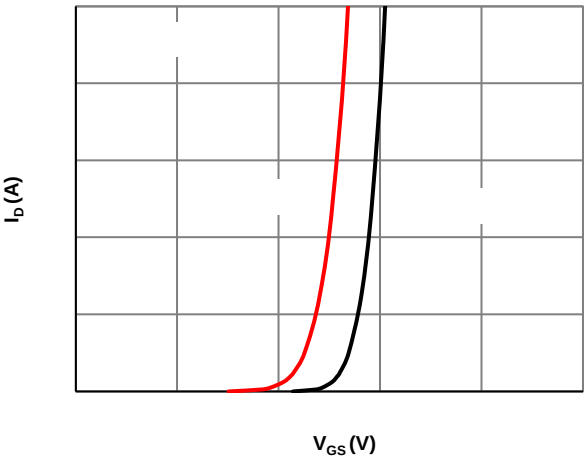


Figure 2: Transfer Characteristics

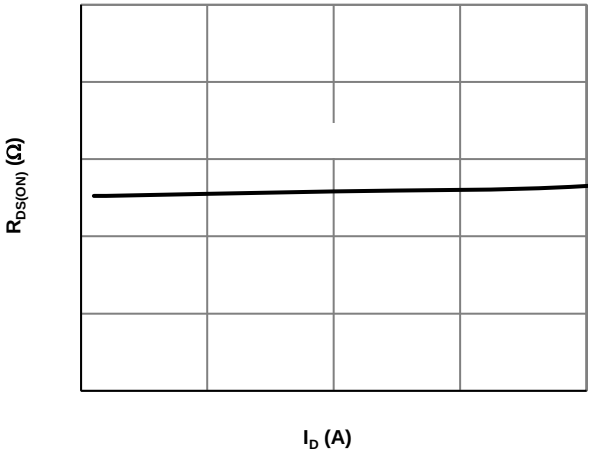


Figure 3: $R_{DS(ON)}$ vs. Drain Current

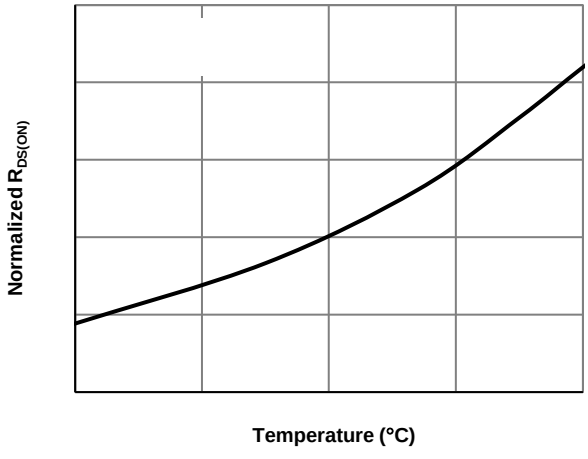


Figure 4: $R_{DS(ON)}$ vs. Junction Temperature

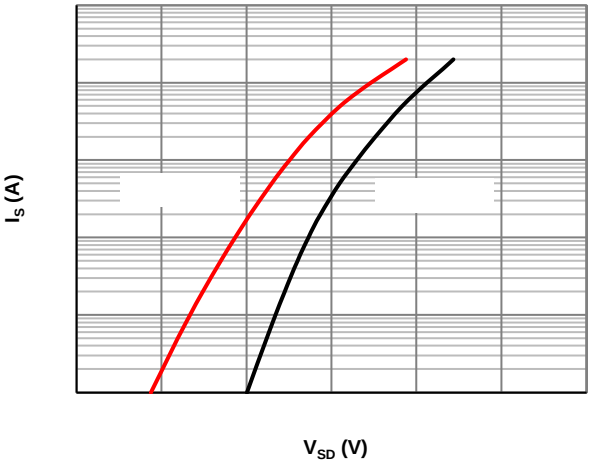


Figure 5: Body-Diode Characteristics

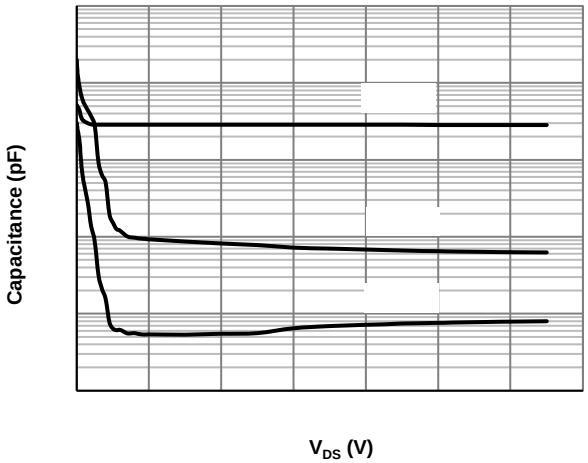


Figure 6: Capacitance Characteristics

Typical Electrical & Thermal Characteristics

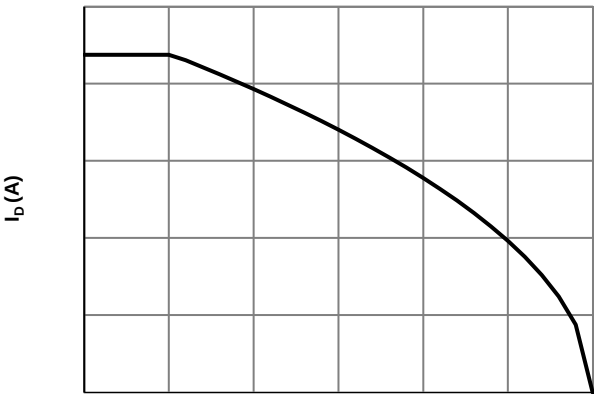


Figure 7: Current De-rating

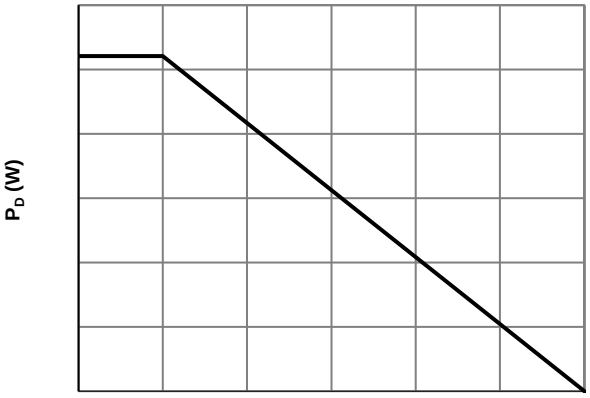


Figure 8: Power De-rating

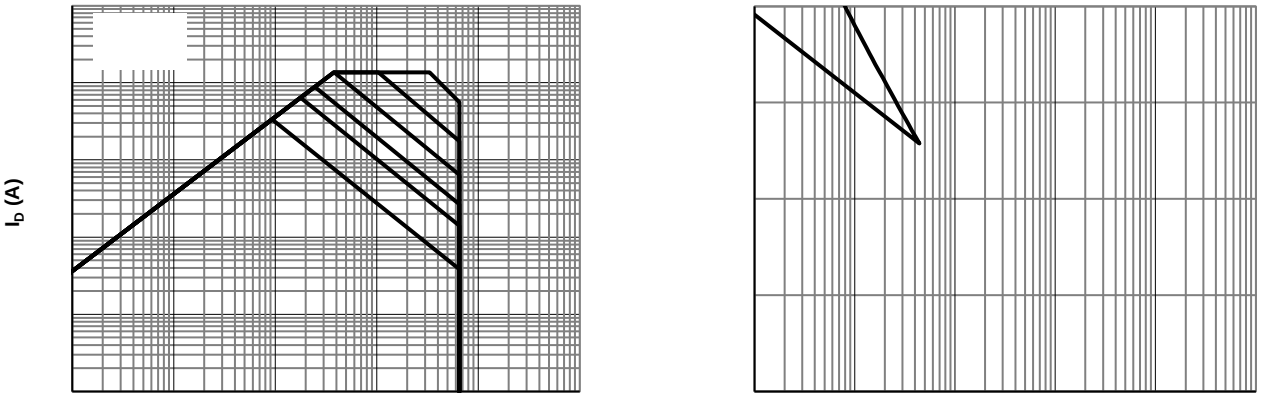
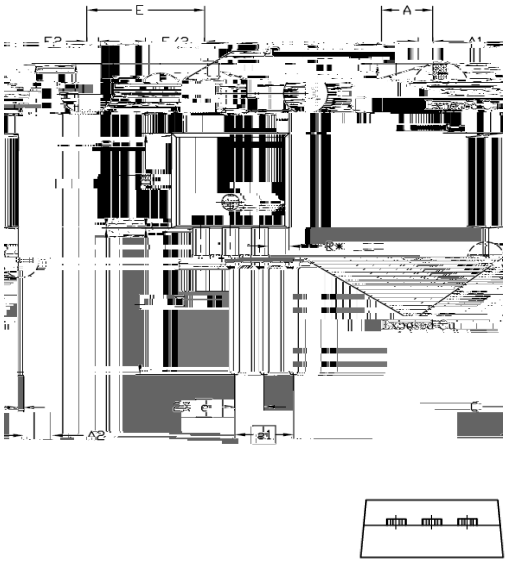
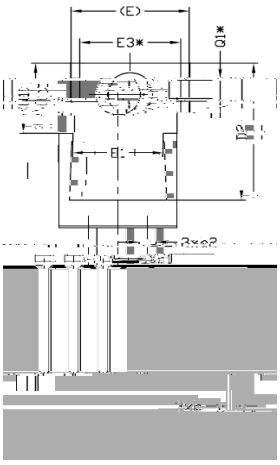


Figure 9: Maximum Safe Operating Area

TO-220-3L Package Information

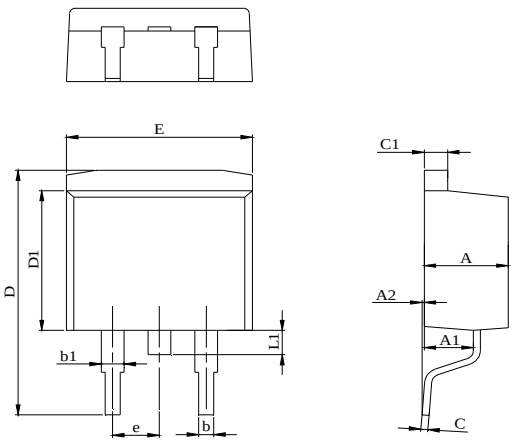




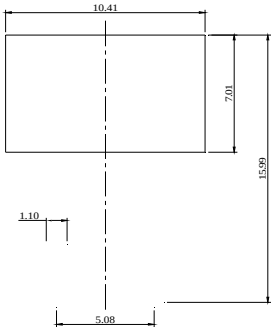
NOTES	SYMBOL	MIN	NOM	MAX
	A	4.24	4.44	4.64
	A1	1.15	1.27	1.40
	A2	2.30	2.48	2.70
	b	0.70	0.80	0.90
	b1	1.20	1.55	1.75
	b2	1.20	1.45	1.70
	c	0.40	0.50	0.60
4	D	14.70	15.37	16.00
	D1	8.82	8.92	9.02
5	D2	12.43	12.73	12.83
	E	9.96	10.16	10.36
	E1	8.30	8.50	8.70
	E2*		8.60REF	
	e		2.54BSC	
	e1		5.08BSC	
5,6	N	3	3	3
	L	13.47	13.72	13.97
	L1	3.60	3.80	4.00
	ØP	3.75	3.84	3.93
	Q	2.60	2.80	3.00
	Q1*		1.73REF	
	e2*		1.83REF	

TO-263-3L Package Information

Package Outline



Recommend Soldering Footprint



DIMENSIONS: MILLIMETERS